

**WHAT IS CLAIMED IS:**

1. A fabricating method of a liquid crystal display, comprising:  
forming a thin film transistor at an area where a gate line crosses a data line;  
forming a protective film to cover a substrate where the thin film transistor is formed;  
simultaneously forming a perforation hole and a contact hole by selectively eliminating the protective film using a partial exposure mask; and  
forming a pixel electrode contacting a gate insulating film and a drain electrode of the thin film transistor through the perforation hole and the contact hole respectively.

2. The fabricating method according to claim 1, wherein forming the thin film transistor includes:  
forming the gate line and a gate electrode on the substrate;  
forming the gate insulating film on the substrate to cover the gate electrode and the gate line;  
forming a semiconductor layer on the gate insulating film; and  
forming a source electrode and the drain electrode on the substrate where the semiconductor layer is formed.

3. The fabricating method according to claim 2, wherein the contact hole extends through the protective film to expose the drain electrode.

4. The fabricating method according to claim 2, wherein the perforation hole exposes the gate insulating film that overlaps the gate line.

5. The fabricating method according to claim 3, wherein the partial exposure mask includes a full exposure area, a shielding area and a partial exposure area.

6. The fabricating method according to claim 5, wherein forming the perforation hole and the contact hole includes:  
depositing a photoresist on the substrate where the protective film is formed;

eliminating the photoresist formed on the drain electrode and forming a photoresist pattern with a first area on the gate line and a photoresist pattern with a second area elsewhere by photolithography using the partial exposure mask at the same time; and

eliminating an area of the protective film corresponding to the drain electrode and an area of the protective film corresponding to the first area using the photoresist pattern as a mask.

7. The fabricating method according to claim 6, wherein the first area in the photoresist pattern corresponds to the partial exposure area of the mask and the second area corresponds to the shielding area.

8. The fabricating method according to claim 5, wherein the thickness of an area of the protective film corresponding to the partial exposure area is about 70% of the thickness of an area of the protective film corresponding to the shielding area.